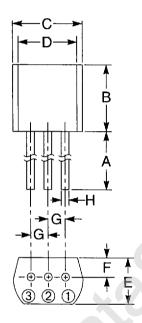


Silicon Bilateral Switch

OUTLINE DRAWING



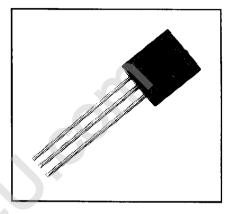
CONNECTION DIAGRAM

- ① TERMINAL 1
- 2 GATE
- ③ TERMINAL 2



Outline Drawing

Dimensions	Inches	Millimeters	
Α	0.492 Min.	12.5 Min.	
В	0.13 Max.	3.3 Max.	
С	0.17	4.3	
D	0.14	3.55	
E	0.098 Max.	2.5 Max.	
F	0.035	0.9	
G	0.049 ± 0.012	1.25	
Н	0.018	0.45	



Description:

The BS08A bilateral switch is a silicon planar monolithic integrated circuit with the electrical characteristics of a bilateral thyristor. The device is designed to switch at 7 to 9 volts with a 0.01%/°C temperature coefficient and have excellently matched characteristics in both directions.

Features:

- Low Switching Voltage of 7 to 9 Volts
- Excellent Switching Voltage Temperature Characteristics (0.01%/°C)
- ☐ High Reliability Devices
- Gate Electrode Facilitating Switching Operation Control and Synchronization.

Applications:

 Trigger Circuits for Thyristor or Triac, Oscillators, Timers

Ordering Information:

Example: Select the complete five digit part number you desire from the table - i.e. BS08A is a 175mA Silicon Bilateral Switch.

	Туре	-	
1/4	BS08A		



BS08A Silicon Bilateral Switch

Absolute Maximum Ratings, $T_a = 25$ °C unless otherwise specified

Ratings	Symbol	BSO8A	Units
DC Forward Anode Current	lΤ	175	mA
Repetitive Peak Forward Current	etitive Peak Forward Current -		Amperes
(1% Duty Cycle, 10μs Pulsewidth), T _a = 100°C			
Non-repetitive Peak Forward Current (10µs Pulsewidth)		2.0	Amperes
Power Dissipation P _T		250	mW
DC Gate Current	l _G	5	mA
Storage Temperature T _{stg}		-55 to 125	°C
Operating Temperature	T _i	-55 to 125	°C

Electrical and Thermal Characteristics, $T_j = 25$ °C unless otherwise specified

				BS08A		
Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Switching Voltage	٧s	T _a = 25°C	7	8	9	Volts
Switching Current	IS	T _a = 25°C	_		200	μΑ
Absolute Switching Voltage Difference	V _{S1} -V _{S2}	T _a = 25°C	_	-	0.5	Volts
Absolute Switching Current Difference	I _{S1} -I _{S2}	T _a = 25°C	_		100	μΑ
Holding Current	1 _H	T _a = 25°C		-	1.5	mA
Off-state Current	l _D	$V_D = 5V, T_a = 25^{\circ}C$	-	_	1.0	μA
		$V_D = 5V, T_a = 85^{\circ}C$	***	_	10	μΑ
Temperature Coefficient of Switching Voltage	ge –	T _a = -55 to 85°C	_	±0.01	_	%/°C
Peak On-state Voltage	V _T	I _T = 175mA, T _a = 25°C	_	_	1.4	Volts
Gate Trigger Current	l _{GT}	V _D = 5V, T _a = 25°C	10	_	200	μΑ
Gate Non-trigger Voltage	V _{GD}	V _D = 5V, T _a = 85°C	0.2	_	=	Volts



BS08A Silicon Bilateral Switch

V_D = 5V

20

40

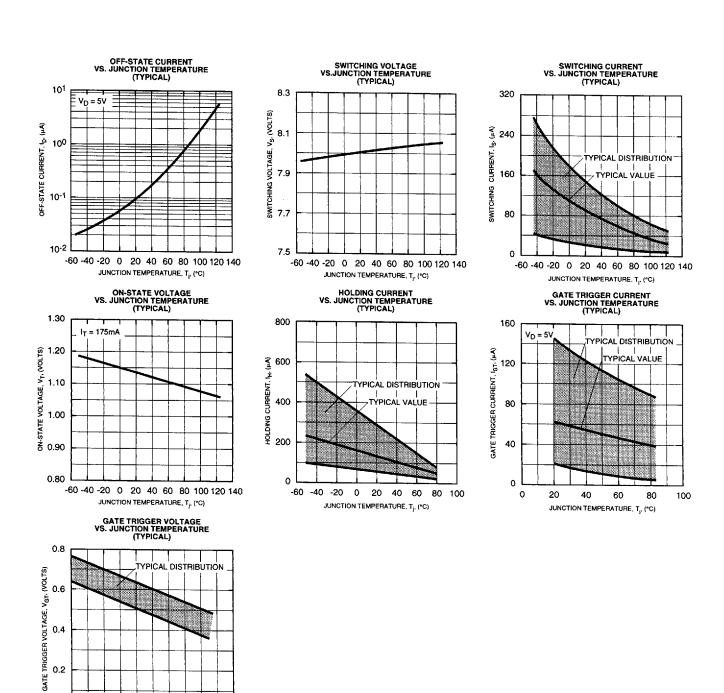
60

JUNCTION TEMPERATURE, T_{j.} (°C)

80

100

0

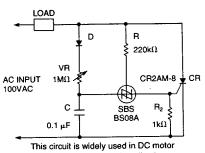




Silicon Bilateral Switch

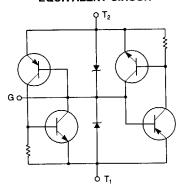
APPLICATION EXAMPLES

THYRISTOR TRIGGER CIRCUIT

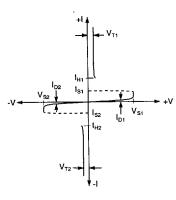


contol and other control applications.

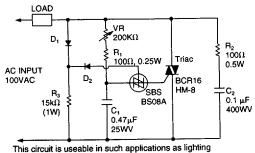
EQUIVALENT CIRCUIT



STATIC CHARACTERISTICS

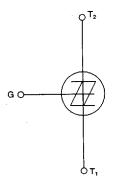


TRIAC TRIGGER CIRCUIT

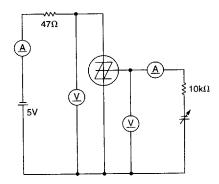


control circuits, electric heater control, and other load control applications.

CIRCUIT SYMBOL



GATE CHARACTERISTICS **MEASUREMENT CIRCUIT**



T-91-01

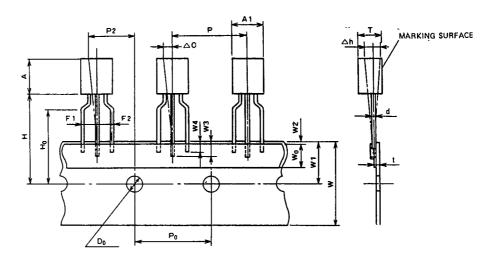
Powerex, Inc., Hillis Street, Youngwood, Pennsylvania 15697 (412) 925-7272
Powerex Europe, S.A., 428 Avenue G. Durand, BP107, 72003 Le Mans, France (43) 41.14.14

Taping

STANDARD SPECIFICATIONS FOR TAPING OF MOLDED PACKAGE THYRISTORS AND TRIACS

TO-92 Package

Thyristor CR02AM, CR03AM, CR04AM Triac BCR1AM



Taping dimensions

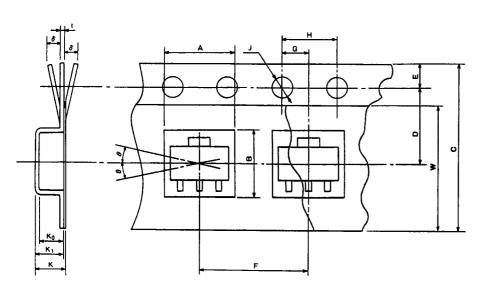
Description of symbol	Symbol	Dimensions (Unit:mm)	Remark
Product width	A1	5.0 MAX	
Product height	Α	5.0 MAX	
Product thickness	Т	3.7 MAX	
Lead wire diameter	d	' 0.6 MAX	
Sticker lead wire length (1)	W3	2.5 MIN	
Sticker lead wire length (2)	W4	2.0 MIN	
Pitch between products	Р	12.7 ± 1.0	
Feed hole pitch	Po	12.7 ± 0.3	The cumulative pitch error is ±1mm per 20 pitches.
Feed hole deviation (1)	P2	6.35 ± 1.3	
Distance between lead wires	F1, F2	2.5 ± 0.4	
Defective product (1)	∆h	0 ± 2.0	·
Tape width	w	18.0 ± 1.0	
Sticker tape width	Wo	6.0 ± 0.5	
Feed hole deviation (2)	W1	9.0 ± 0.5	
Sticker tape deviation	W2	0.5 MAX	
Position of product bottom surface	Н	17.5 MIN	
Lynch height of lead wire	H₀	16.0 ± 0.5	
Feed hole diameter	D ₀	4.0 ± 0.2	
Tape thickness	t	0.7 ± 0.2	
Defective product (2)	ΔC	0 ± 1.0	



T-91-01

Powerex, Inc., Hillis Street, Youngwood, Pennsylvania 15697 (412) 925-7272 Powerex Europe, S.A., 428 Avenue G. Durand, BP107, 72003 Le Mans, France (43) 41.14.14

Powerex Semiconductor Data Book Taping



SOT-89 Package

Thyristor CR08AS

Taping dimensions

Description of symbol		Symbol	Dimensions/angles Unit:mm	Remark	
Parts insertion	Height	Α	5.0 ± 0.1	Cross-section of the surface 0.5mm above the inner bottom	
Concave square hole	Width	В	4.6 ± 0.1	Cross-section of the surface 0.5mm above the inner bottom	
	Depth	K ₀	1.8 ± 0.1	Inner space	
	Pitch	F	8.0 ± 0.1	Cumulative error +0.1/-0.3 MAX/10 pitches	
	Diameter	J	ϕ 1.5 $\pm^{0.1}_{0.05}$		
Round feed hole	Pitch	Н	4.0 ± 0.1	Cumulative error +0.1/-0.3 MAX/10 pitches	
	Position	E	1.5 ± 0.1	Distance between the tape edge and the hole center	
Distance between center lines	Vertical	G	2.0 ± 0.5	Center line of concave square hole and round feed hole	
	Horizontal	D	5.65 ± 0.05	Center line of concave square hole and round feed hole	
Cover tape	Width	w	9.5 + 0.3/-0	Thickness: 0.1 MAX	
-	Width	С	12±0.2	Warp δ0.3 MAX	
Carrier tape	Thickness	t	0.3 ± 0.05		
	Package hole depth	K ₁	2.1 ± 0.1		
Device	Package dimensions	1- 1	_	As shown in (e)	
	Inclination	θ	30° MAX.	-	
Total Thickness		к	2.3 ± 0.1	Total thickness including cover and carrier tapes	